



PTO/SB/08 Equivalent

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Multiple sheets used when necessary)

SHEET 1 OF 2

Application No.	10/799,335
Filing Date	12 March 2004
First Named Inventor	Pierre Tomasini
Art Unit	2812
Examiner	Unknown
Attorney Docket No.	ASMEX.447A

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear
GAR	1	6,875,279	04/2005	Chu et al.	
	2	2003/0445063	03/2003	Hernandez et al.	
	3	2003/0082300	05/2003	Todd et al.	
	4	2003/0124818	07/2003	Luo et al.	
	5	2003/0157787	08/2003	Murthy et al.	
	6	2003/0207127	11/2003	Murthy et al.	
	7	2003/0235931	12/2003	Wada et al.	
	8	2005/0079692	04/2005	Samoilov et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials	Cite No.	Foreign Patent Document Country Code-Number-Kind Code Example: JP 1234567 A1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear	T ¹
GAR	9	EP 0858101	02/1998	Aoyama, Tohru		
	10	WO 00/15885	03/2000	Hernandez et al.		

NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
GAR	11	CANNON, D. et al., "Tensile strained epitaxial Ge films on Si(100) substrates with potential application in L-band telecommunications," Applied Physics Letter, Volume 84, Number 6, February 9, 2004, pp. 906-908	
	12	COLACE, L. et al., "Efficient high-speed near-infrared Ge photodetectors integrated on Si substrates," Applied Physics Letters, Volume 76, Number 10, March 6, 2000, pp. 1231-1233	
	13	COLACE, L. et al., "Ge-on-Si Approaches to the Detection of Near-Infrared Light," IEEE Journal of Quantum Electronics, Vol. 35, No. 12, December 1999, pp. 1843-1852	
	14	FAMA, S. et al., "High performance germanium-on silicon detectors for optical communications," Applied Physics Letters, Volume 81, Number 4, July 22, 2002, pp. 586-588	
	15	HULL, R., "Metastable strained layer configurations in the SiGe/Si System," (1999) <u>EMIS Datareviews, Series No. 24 of SiGe and SiGe:C</u> , edited by Erich Kasper et al., INSPEC (2000), London, UK	
	16	ISHIKAWA, Y. et al., "Strain-induced band gap shrinkage in Ge grown on Si substrate," Applied Physics Letters, Volume 82, Number 12, March 31, 2003, pp. 2044-2046	
	17	LEE et al., "Growth of strained Si and strained Ge heterostructures on relaxed Si _{1-x} Ga _x by ultrahigh vacuum chemical vapor deposition," J. Vac. Sci. Technol. B 22(1) (Jan/Feb 2004).	

Examiner Signature

Date Considered

5/26/06


*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

T¹ - Place a check mark in this area when an English language Translation is attached.

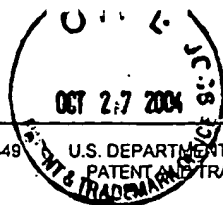
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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ¹
GNR	18	LI, Q. et al., "Selective growth of Ge on Si(100) through vias of SiO ₂ nanotemplate using solid source molecular beam epitaxy," Applied Physics Letters, Volume 83, Number 24, December 15, 2003, pp. 5032-5034	
	19	LIU, J. et al., "Silicidation -induced band gap shrinkage in Ge epitaxial films on Si," Applied Physics Letters, Volume 84, Number 5, February 2, 2004, pp. 660-662	
	20	MASINI, G. et al., "High-Performance p-i-n Ge on Si Photodetectors for the Near Infrared: From Model to Demonstration," IEEE Transactions of Electron Devices, Vol. 48, No. 6, June 2001, pp. 1092-1096	
	21	SCHOLLHORN et al., "Coalescence of germanium islands on silicon," Thin Solid Films, " Vol. 336 (1988), pp. 109-111	

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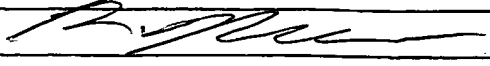
FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. ASMEX.447A	APPLICATION NO. 10/799,335
	APPLICANT Tomasini, et al.	
	FILING DATE March 12, 2004	GROUP 2812

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
BNR	1	6,646,073	04/2003	Kondo			
	2	6,709,901	03/2004	Yamazaki, et al.			
	3	2002/0173130	11/2002	Pomerode, et al.			

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	4							
	5							
	6							

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)						
	7						
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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
<i>GM</i>	1	3,602,778	08/31/71	Ura, et al			
	2	3,720,877	03/13/73	Zarowin			
	3	3,729,645	04/24/73	Redington			
	4	3,737,739	06/05/73	Blakeslee, et al.			
	5	3,984,718	10/05/76	Fein, et al.			
	6	3,984,857	10/05/76	Mason			
	7	3,985,590	10/12/76	Mason			
	8	4,461,820	07/24/84	Shirai, et al.			
	9	4,656,013	04/07/87	Hiai, et al.			
	10	4,699,892	10/13/87	Suzuki			
	11	4,786,574	11/22/88	Shirai, et al.			
	12	4,803,186	02/07/89	Chen, et al.			
	13	4,857,270	08/15/89	Maruya, et al.			
	14	4,868,014	09/19/89	Kanai, et al.			
	15	4,983,274	01/08/91	Chen, et al.			
	16	5,037,775	08/06/91	Reisman			
	17	5,112,439	05/12/92	Reisman, et al.			
	18	5,281,274	01/25/94	Yoder			
	19	5,281,299	01/25/94	Escoffier, et al.			
	20	5,294,285	03/15/94	Kanai, et al.			
	21	5,316,958	05/31/94	Meyerson			
	22	5,366,554	11/22/94	Kanai, et al.			
	23	5,482,557	01/09/96	Kanai, et al.			
	24	5,576,247	11/19/96	Yano, et al.			
	25	5,646,073	07/08/97	Grider, et al.			
	26	5,667,586	09/16/97	Ek, et al.			
	27	5,818,100	10/06/98	Grider, et al.			

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FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
ASMEX.447AAPPLICATION NO.
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BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

APPLICANT
Tomasini, et al.FILING DATE
March 12, 2004GROUP
2812

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
GNR	28	6,242,080 B1	06/05/01	Kondo			
	29	6,451,641 B1	09/17/02	Halliyal, et al.			
	30	6,515,219 B2	02/04/03	Kondo			
	31	2003/0010978 A1	01/16/03	Burden			
	32	2003/0111013 A1	06/19/03	Oosterlaken, et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
GNR	33	JP 62017004	01/26/87	Japan			abstract	only

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
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EXAMINER <i>E. Mue</i>	DATE CONSIDERED <i>5/26/04</i>
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